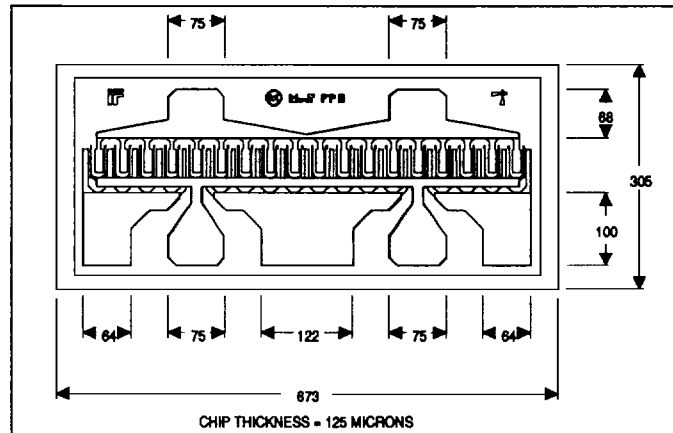


# MwT-A8

## 16 GHz High Power GaAs FET

- 0.6 WATT POWER OUTPUT AT 12 GHz
- +40 dBm THIRD ORDER INTERCEPT
- HIGH ASSOCIATED GAIN
- 0.3 MICRON REFRACTORY METAL/GOLD GATE
- 1200 MICRON GATE WIDTH
- DIAMOND-LIKE CARBON PASSIVATION
- CHOICE OF CHIP AND ONE PACKAGE TYPE

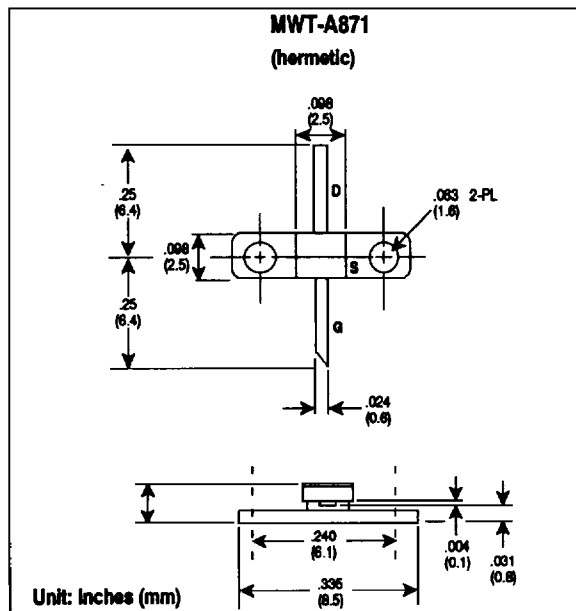


### DESCRIPTION

The MwT-A8 GaAs MESFET is ideally suited to narrow-band applications such as cellular telephone, PCN, point-to-point communications links, and other wireless applications as the driver transistor for the output power amplifier. The third-order intercept performance of the MwT-A8 is excellent, typically 12 dB above the 1 dB compression point. The chip is produced using MwT's reliable metal system and all devices are screened to insure reliability. All chips are passivated using MwT's patented "Diamond-Like Carbon" process for durability with no degradation in performance. Designers can use MwT's unique BIN selection feature to choose devices from narrow Idss ranges, insuring consistent circuit operation.

### RF SPECIFICATIONS AT Ta = 25°C

SYMBOL	PARAMETERS AND CONDITIONS	FREQ	UNITS	MwT-A8 SP MwT-A871 SP		MwT-A8 HP MwT-A871 HP	
				MIN	TYP	MIN	TYP
P1dB	Output Power at 1dB Compression VDS=6.0 V IDS= 180 mA	12 GHz	dBm	26.0	27.0	27.0	28.0
SSG	Small Signal Gain VDS=6.0 V IDS= 180 mA	12 GHz	dB	7.0	7.5	7.5	8.0
PAE	Power Added Efficiency VDS=6.0 V IDS= 180 mA	12 GHz	%	20	30	25	35
IDSS	Recommended IDSS Range for Optimum P1dB		mA		240-380		320-440



**DC SPECIFICATIONS AT Ta = 25 °C**

SYMBOL	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
<b>Idss</b>	Saturated Drain Current Vds=4.0 V VGS=0.0 V	mA	120		480
<b>Gm</b>	Transconductance Vds=2.0 V VGS=0.0 V	mS	144	160	
<b>Vp</b>	Pinch-off Voltage Vds=3.0 V IDS=8.0 mA	V		-2.0	-5.0
<b>BVGSO</b>	Gate-to-Source Breakdown Voltage Igs=-0.8 mA	V	-6.0	-12.0	
<b>BVGDO</b>	Gate-to-Drain Breakdown Voltage Igd=-0.8 mA	V	-8.0	-12.0	
<b>Rth</b>	Thermal Resistance* MwT-A8 Chip MwT-A871	°C/W		50 50	

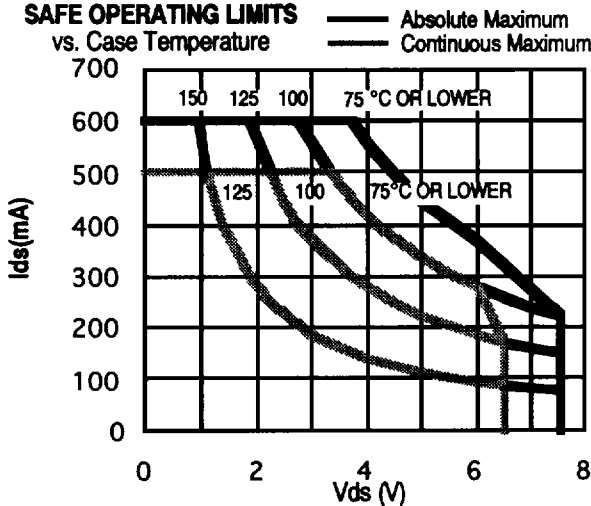
\* Overall Rth depends on case mounting

**MAXIMUM RATINGS AT Ta = 25 °C**

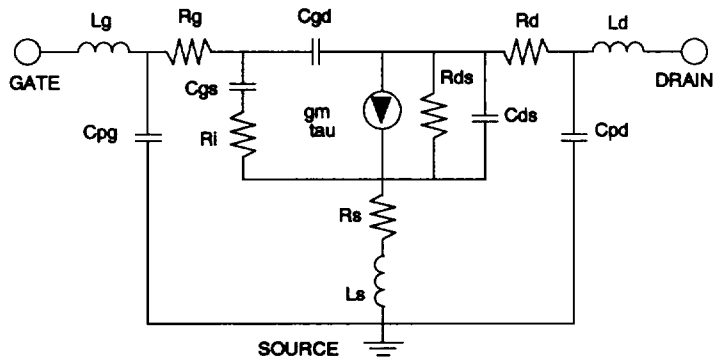
SYMBOL	PARAMETER	UNITS	CONT MAX <sup>1</sup>	ABSOLUTE MAX <sup>2</sup>
VDS	Drain to Source Voltage	V	See Safe Operating Limits	
Tch	Channel Temperature	°C	+150	+175
Tst	Storage Temperature	°C	-65 to +150	+175
Pin	RF Input Power	mW	480	720

NOTES: 1. Exceeding any one of these limits in continuous operation may reduce the mean-time-to-failure below the design goals.  
2. Exceeding any one of these limits may cause permanent damage.

**SAFE OPERATING LIMITS vs. Case Temperature**



**DEVICE EQUIVALENT CIRCUIT MODEL**

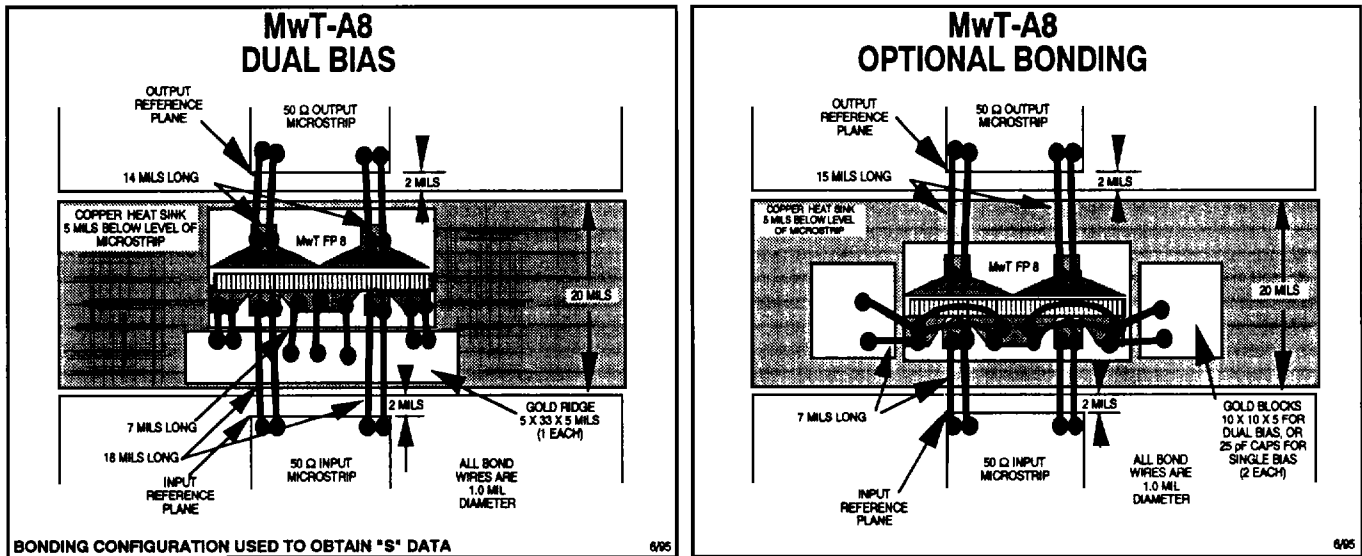


PARAMETER		VALUE
Gate Bond Wire Inductance	Lg	.142 nH
Gate Pad Capacitance	Cpg	.18 pF
Gate Resistance	Rg	.64 Ω
Gate-Source Capacitance	Cgs	1.19 pF
Channel Resistance	Ri	2.05 Ω
Gate-Drain Capacitance	Cgd	.10 pF
Transconductance	gm	145 mS
Transit time	tau	1.8 psec

PARAMETER		VALUE
Source Resistance	Rs	.26 Ω
Source Inductance	Ls	.031 nH
Drain-Source Resistance	Rds	70 Ω
Drain-Source Capacitance	Cds	.075 pF
Drain Resistance	Rd	0.48 Ω
Drain Pad Capacitance	Cpd	.209 pF
Drain Inductance	Ld	.118 nH

## RECOMMENDED ASSEMBLY CONFIGURATION

Shown below is the assembly and bonding configuration used for S-Parameter measurements of the MwT-A8 chip. This configuration is recommended for optimum performance. For single-bias applications the gold blocks may be replaced by capacitors. An additional interconnecting bond would then be required. Contact MwT for additional applications information.



## BIN SELECTION

Every MwT-A8 wafer has been probed for Idss and the data stored on computer disk. Customers may select from Idss values in any of 18 current bins, as shown below, to insure consistent performance in their circuit. The shaded bins are typically available in smaller quantity and caution is advised before designing these bins into high production applications. MwT's "Smart Wafer Picker" reads the stored Idss Data from the disk and devices from customer selected bins are quickly and automatically picked from the wafer and loaded into shipping containers.

BIN#	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
IDSS (mA)	120-140	140-160	160-180	180-200	200-220	220-240	240-260	260-280	280-300	300-320	320-340	340-360	360-380	380-400	400-420	420-440	440-460	460-480

## BIN ACCURACY

Due to the effects of temperature, dc loading and probe tip varnishing, the IDSS from the "on wafer" probing of any MwT device may differ after it has been attached to a proper heat sink and tested in an RF or DC circuit.

Because of the aforementioned effects, the IDSS distribution may deviate as much as +/- 1 bin within the range identified on the label of each die shipping container, and +/- 2 bins within the selected range.

## TYPICAL COMMON SOURCE SCATTERING PARAMETERS

MwT-A8 CHIP: VDS = 6.0 V, IDS = 0.6, IDSS = 230 mA

FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.00	.96	-61.1	7.00	142.2	.03	57.8	.20	-60.0
2.00	.90	-101.2	5.16	117.4	.05	38.0	.22	-93.1
3.00	.87	-125.4	3.89	101.1	.06	26.9	.24	-109.4
4.00	.85	-141.1	3.06	89.1	.06	20.2	.26	-118.3
5.00	.84	-152.2	2.50	79.4	.06	15.7	.28	-124.1
6.00	.84	-160.6	2.11	70.9	.06	12.6	.31	-128.4
7.00	.84	-167.5	1.81	63.3	.06	10.2	.34	-132.2
8.00	.84	-173.2	1.59	56.3	.06	8.4	.36	-135.7
9.00	.84	-178.2	1.40	49.8	.06	7.0	.40	-139.1
10.00	.84	177.4	1.26	43.5	.06	5.9	.42	-142.4
12.00	.83	169.5	1.04	31.9	.06	4.3	.48	-148.9
14.00	.83	162.7	0.87	21.1	.06	3.2	.52	-155.4
16.00	.84	156.6	0.75	11.1	.07	2.2	.57	-161.8
20.00	.84	145.5	0.57	-6.8	.07	0.3	.65	-174.0

MwT-A871HP: VDS = 6.0 V, IDS = 180 mA

FREQUENCY (GHz)	S11		S21		S12		S22		MSG dB
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
1.00	.88	-79.2	7.13	124.2	.04	39.1	.25	-62.2	22.2
2.00	.81	-125.4	4.88	90.2	.06	17.2	.23	-95.3	19.4
3.00	.79	-153.5	3.53	64.9	.06	3.9	.24	-116.1	17.5
4.00	.80	-173.7	2.79	43.9	.07	-4.5	.27	-133.4	16.1
5.00	.80	168.8	2.31	26.4	.08	-15.3	.32	-150.8	14.6
6.00	.83	154.4	2.00	9.4	.08	-22.5	.36	-166.0	13.8
7.00	.84	140.9	1.85	-6.3	.09	-31.9	.39	-179.2	13.0
8.00	.86	129.1	1.69	-20.9	.11	-41.7	.45	-163.9	11.8
9.00	.88	116.9	1.72	-38.1	.12	-62.3	.49	-147.2	11.5
10.00	.89	103.4	1.60	-54.5	.13	-74.5	.53	-131.9	10.8
11.00	.86	90.5	1.54	-72.4	.14	-85.9	.55	-117.2	10.6
12.00	.85	83.4	1.51	-86.0	.13	-96.5	.56	-104.5	10.4

### DEVICE HANDLING PROCEDURE

- 1) Open package in clean room environment only.
- 2) GaAs FETs are sensitive to electrostatic discharge. Precautions should be taken in handling, die attachment, and bonding to assure that Maximim Ratings are not exceeded as a result of electrical discharge.
- 3) Chips have been cleaned and are ready for die attachment. DO NOT attempt to re-clean.
- 4) Assembly should be performed with parts no hotter than 300° C. All circuit components (such as resistors and capacitors) should be assembled completely before the FET is die attached. Assembly should be performed as quickly as possible. In general, no chip should be left at 300°C for over 2 minutes.
- 5) Die attach with clean AuSn alloy under forming gas at 280 to 300° C. Scrub chip down with tweezers. Thermal resistance is critically dependent on this operation.
- 6) Thermasonic wedge bonding is recommended. A .0015 in. bond flat wedge at 125 to 150° C should be used with a heater stage temperature of 200 to 225° C. Apply 15 to 20 grams of bond force to .001 in. diameter gold wire with an elongation of 2 to 5%.
- 7) Store in a clean, dry, inert environment such as nitrogen at room temperature.
- 8) CAUTION: Handling of chips other than as specified above may cause permanent damage.